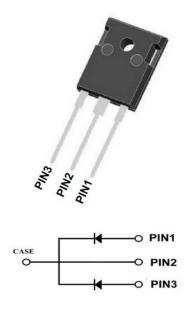




Silicon Carbide Schottky Diode

V_{RRM}	1200V
I _{F (135°C)}	40A ⁽²⁾
Q _C	182nC ⁽²⁾



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- AEC-Q101 qualified
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

Package: TO-247AB
 Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free

• **Terminals**: Tin plated leads

• Polarity: As marked

■Maximum Ratings (T_C=25°C Unless otherwise specified)

PARAMTETER	SYMBOL	UNIT	VALUE
Device marking code			D112030NCTQG3
Reverse voltage (Repetitive peak) @ T _j =25°C	V_{RRM}	٧	1200
Reverse voltage (Surge peak) @ T _j =25°C	V_{RSM}	V	1200
Reverse voltage (DC) @ T _j =25°C	V _{DC}	V	1200
Continuous forward current @ T _C =25°C			43/86
Continuous forward current @ T _C =135°C	I _F	А	20/40
Continuous forward current @ T _C =150°C			15/30
Non-repetitive peak forward surge current @ T _C =25°C, tp=10ms, Half Sine Wave	I _{FSM}	А	160 ⁽¹⁾
Power Dissipation@ T _C =25°C	D	W	164/326
Power Dissipation@ T _C =110°C	Р _{тот}		71/141
i²t Value@ T _C =25°C ,tp=10ms	∫ i²dt	A ² S	128 ⁽¹⁾
Operating junction and Storage temperature range	T_{j} , T_{stg}	°C	-55 to +175

⁽¹⁾ Per Leg, (2) Per Device



■Electrical Characteristics (Per Leg)

PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.
Forward voltage drop	V _F	٧	I _F =15A, T _j =25°C	1.35	1.55
			I _F =15A, T _j =175°C	1.85	-
Reverse leakage current	I _R	μА	V _R =1200V, T _j =25°C	3	20
			V _R =1200V, T _j =175°C	19	-
Total capacitive charge	Q _C	nC	V_R =800V, T_j =25°C , Q_C = \int_0^{VR} C(V)dV	91	-
	C pF	$\begin{array}{c} V_{R}\text{=}0V\text{, f=}1\text{MHZ} \\ \\ V_{R}\text{=}400V\text{, f=}1\text{MHZ} \\ \\ V_{R}\text{=}800V\text{, f=}1\text{MHZ} \end{array}$	1280	-	
Total capacitance			V _R =400V, f=1MHZ	87	-
			V _R =800V, f=1MHZ	64	-
Capacitance Stored Energy	Ec	μJ	V _R =800V	23	-

■Thermal Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	$R_{\theta J-C}$	°C W	0.91 ⁽¹⁾ 0.46 ⁽²⁾

⁽¹⁾ Per Leg, ⁽²⁾ Per Device

■Typical Characteristics (Per Leg)

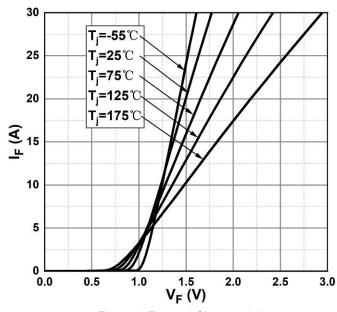


Figure 1. Forward Characteristics

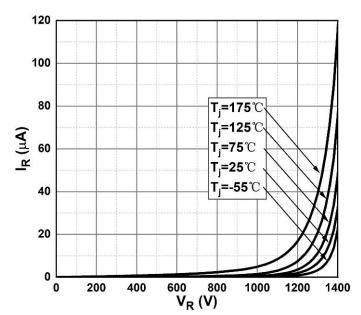
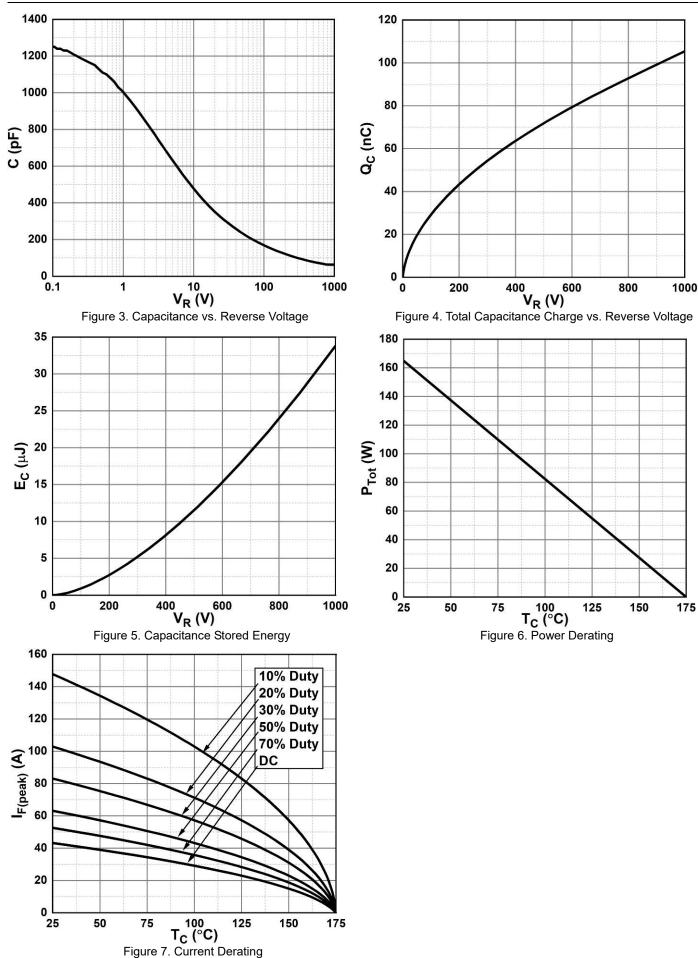


Figure 2. Reverse Characteristics





■Typical Characteristics (Device)

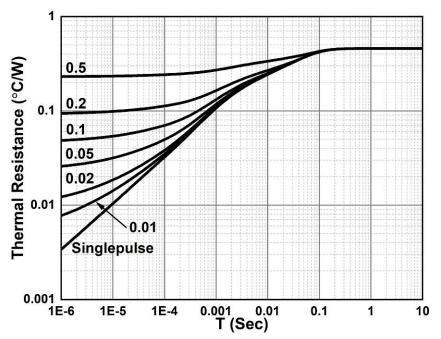
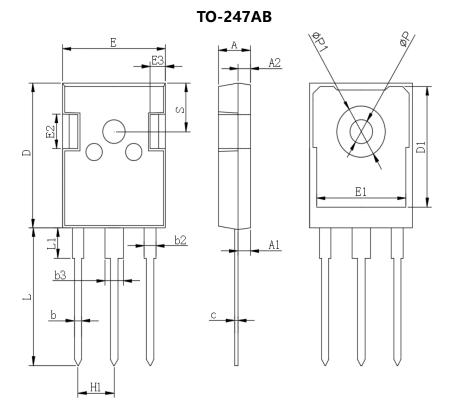


Figure 8. Transient Thermal Impedance





■Outline Dimensions



TO-247AB				
Dim	Min	Max		
Α	4.80	5.20		
A1	2.21	2.61		
A2	1.85	2.15		
b	1.0	1.4		
b2	1.91	2.21		
С	0.5	0.7		
D	20.70	21.30		
D1	16.25	16.85		
Е	15.50	16.10		
E1	13.0	13.6		
E2	4.80	5.20		
E3	2.30	2.70		
L	19.62	20.22		
L1	-	4.30		
ΦР	3.40	3.80		
ФР1	-	7.30		
S	6.15TYP			
H1	5.44TYP			
b3	2.80	3.20		



YJD112030NCTQG3Q



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